



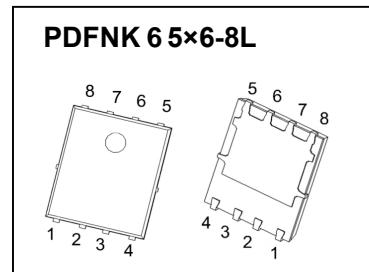
PDFNK 6 5x6-8L Plastic-Encapsulate MOSFETs

AC70SN15 N-Channel Power MOSFET

V_{(BR)DSS}	R_{D(on)}TYP	I_D
150V	10mΩ@10V	70A

DESCRIPTION

The AC70SN15 uses shielded gate trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications



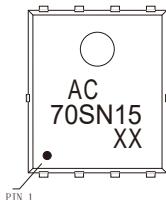
FEATURES

- High Power and current handing capability
 - Load switch
 - High density cell design for ultra low $R_{DS(ON)}$
 - Lead free product is acquired
 - Good stability and uniformity with high E_{AS}
 - Excellent package for good heat dissipation

APPLICATIONS

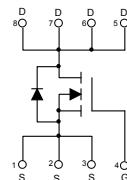
- SMPS and general purpose applications
 - Hard switched and high frequency circuits
 - Uninterruptible Power Supply
 - Power management

MARKING



AC70SN15 = Part No.
Solid dot=Pin1 indicator
XX=Date Code.

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D ^①	70	A
Pulsed Drain Current	I_{DM} ^②	250	A
Single Pulsed Avalanche Energy	E_{AS} ^③	320	mJ
Power Dissipation	P_D ^④	114	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$ ^⑤	62.5	°C/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$ ^⑥	1.1	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS

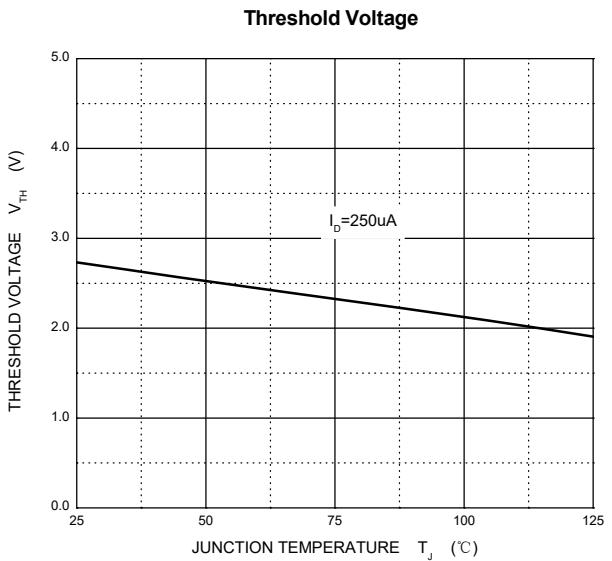
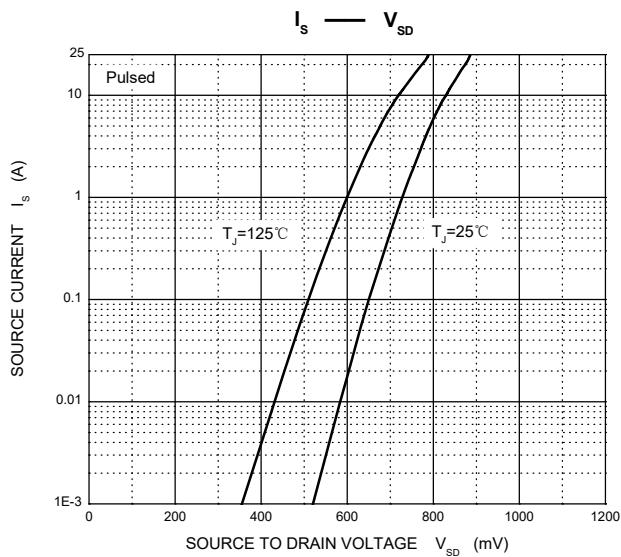
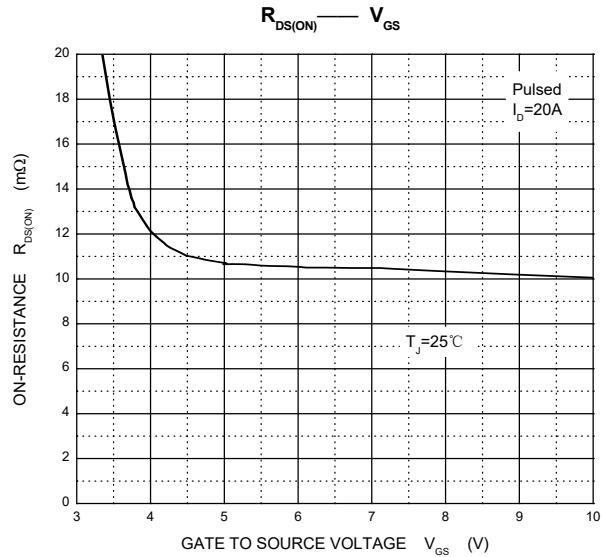
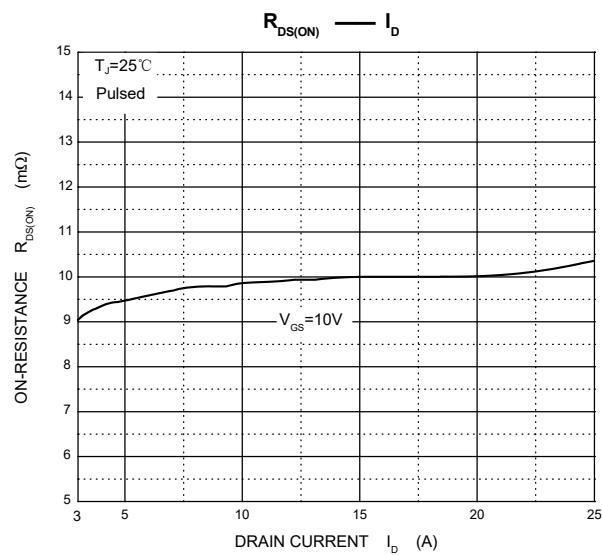
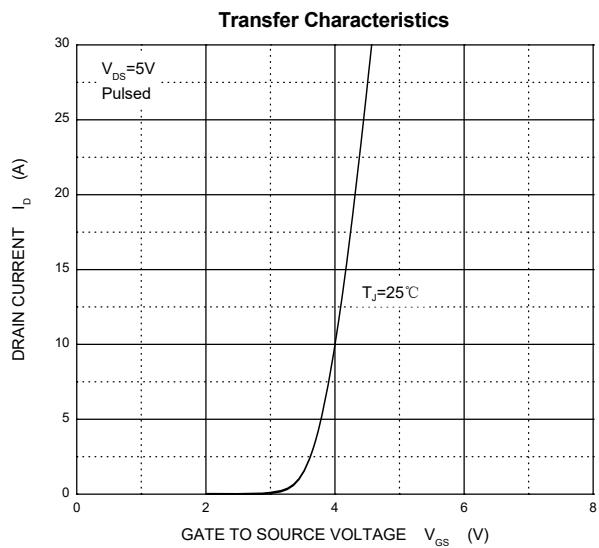
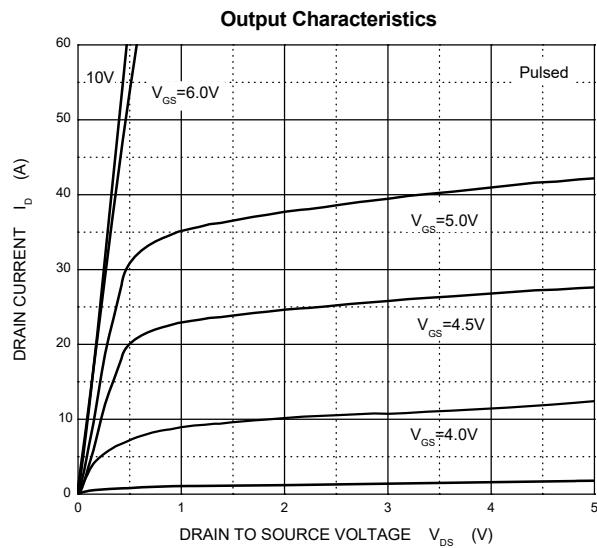
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	150			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 100\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	2.0	2.8	4.0	V
Drain-source on-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		10	12	$\text{m}\Omega$
Gate resistance	R_G	$f = 1\text{MHz}$		3.5		Ω
Dynamic characteristics ^{(4) (5)}						
Total gate charge	Q_g	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		45	98	nC
Gate-source charge	Q_{gs}			10	25	
Gate-drain charge	Q_{gd}			5	12	
Input Capacitance	C_{iss}	$V_{\text{DS}} = 75\text{V}, V_{\text{GS}} = 0\text{V}, f = 100\text{kHz}$		3850	5800	pF
Output Capacitance	C_{oss}			252	430	
Reverse Transfer Capacitance	C_{rss}			7.5	13.5	
SWITCHING PARAMETERS ^{(4) (5)}						
Turn-on delay time	$t_{d(\text{on})}$	$V_{\text{GS}} = 10\text{V}, V_{\text{DS}} = 75\text{V}, R_G = 10\Omega, I_D = 20\text{A}$		19		ns
Turn-on rise time	t_r			9		
Turn-off delay time	$t_{d(\text{off})}$			29		
Turn-off fall time	t_f			11		
Source-Drain Diode characteristics						
Body diode voltage	$V_{SD}^{(4)}$	$I_S = 20\text{A}, V_{GS} = 0\text{V}$			1.3	V
Reverse recovery time	T_{rr}	$V_R = 75\text{V}, I_F = 20\text{A}, dI_F/dt = 100 \text{ A}/\mu\text{s}$		85		ns
Reverse recovery charge	Q_{rr}			165		nC

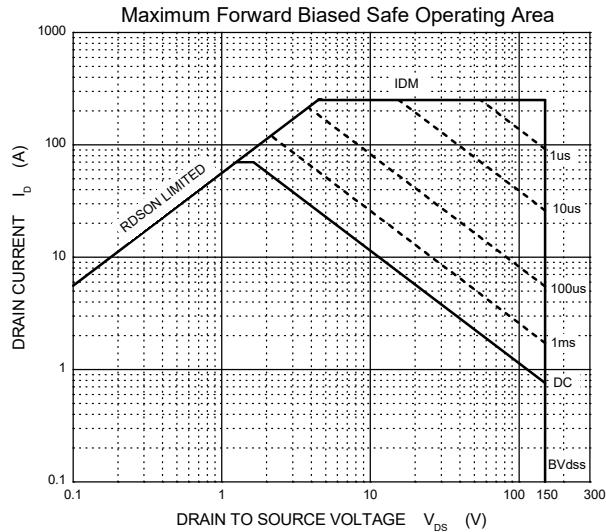
Notes:

1. $T_C = 25^\circ\text{C}$ Limited only by maximum temperature allowed.
2. $P_W \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$.
3. EAS condition: $V_{DD} = 50\text{V}, V_{GS} = 10\text{V}, L = 0.1\text{mH}, R_g = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
4. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
5. Guaranteed by design, not subject to production.
6. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25^\circ\text{C}$.

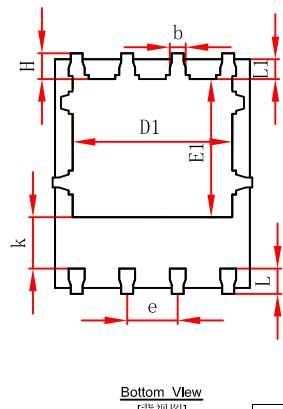
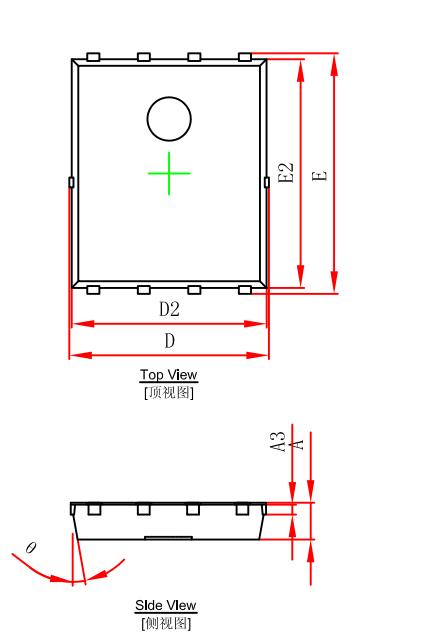
Typical Characteristics



Typical Characteristics

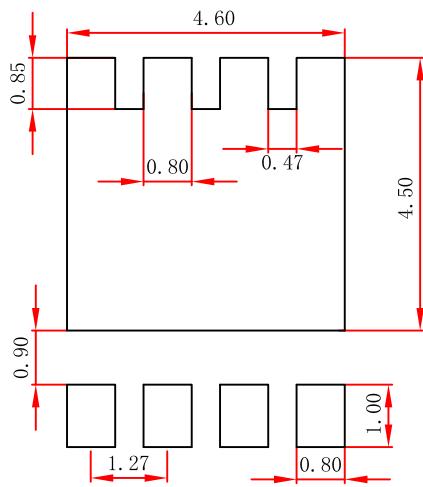


PDFNWB5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
theta	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout

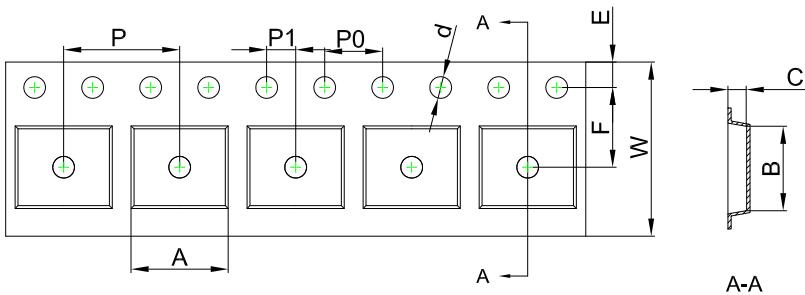


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

PDFNWB5×6 Tape and Reel

PDFNWB5×6-8L Embossed Carrier Tape

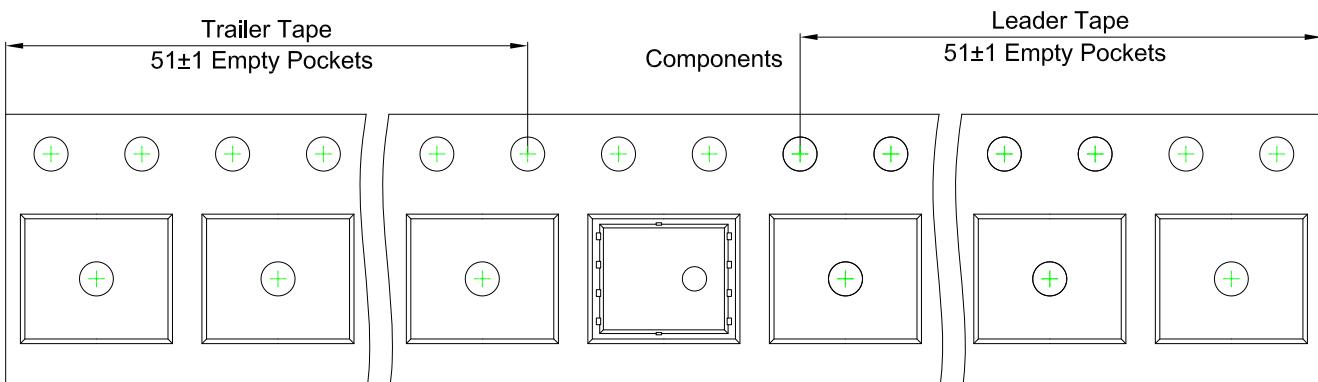


Packaging Description:

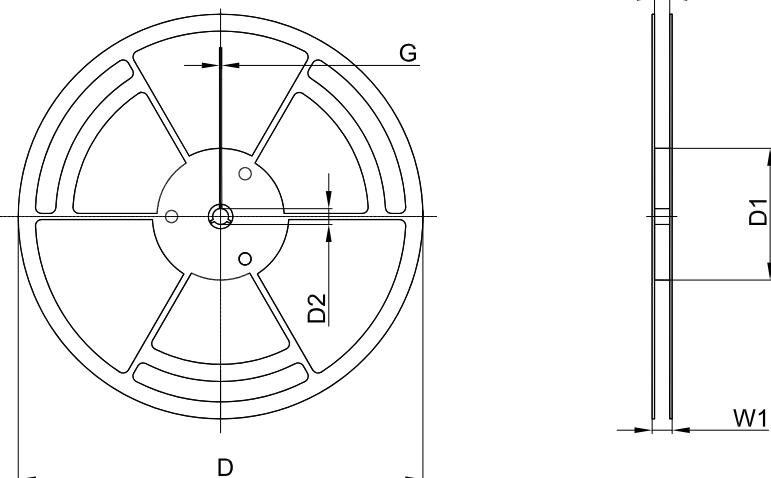
PDFNWB5×6-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFNWB5×6-8L	6.30	5.30	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFNWB5×6-8L Tape Leader and Trailer



PDFNWB5×6-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13" Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365